

ABSTRACT OF THE DISCLOSURE

A semiconductor integrated circuit is provided which includes bump electrodes having a uniform height.

The semiconductor integrated circuit includes: a

5 semiconductor substrate (wafer) having a plurality of bump electrode formation areas and a bump electrode non-formation area respectively defined on a front

surface thereof; a first electrode pad formed in the bump electrode non-formation area; a second electrode

10 pad formed in each bump electrode formation area; and

a bump electrode formed on each second electrode pad;

wherein the first electrode pad is used for supplying a plating electric current to the second electrode pads through the semiconductor substrate in formation of

15 the bump electrodes by electrolytic plating.